FM30H12G

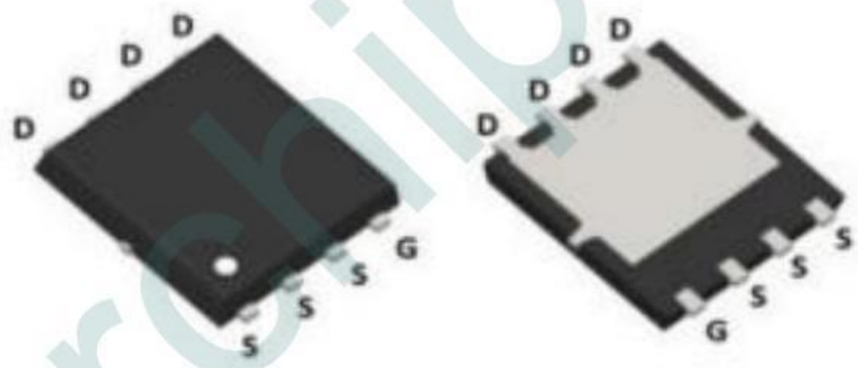
N-Channel Trench Power MOSFET

- 30V,120A
- $R_{DS(ON)}$=2.9mΩ(Typ.) @ V_{GS} =10V
- $R_{DS(ON)}$=3.8mΩ(Typ.) @ V_{GS} =4.5V

Application

- LCD TV
- Notebook
- Elevator
- Inductive heating
- Power tools
- Broadband

Package



PDFN-8

Absolute Maximum Ratings (T_c=25℃unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	120	A
		T_C = 100℃	53	A
I_{DM}	Pulsed Drain Current note1		254	A
E_{AS}	Single Pulsed Avalanche Energy note2		289	mJ
P_D	Power Dissipation	T_C = 25℃	28	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		4.4	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

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